MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet



SOT - 23



1 8495

2. EMITTER

3. COLLECTOR

TRANSISTOR (NPN)

FEATURES

Complementary to MMBT3906-MS

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

MARKING: 1AM

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	٧
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current	200	mA
Pc	Collector Power Dissipation	200	mW
R _{OJA}	Thermal Resistance From Junction To Ambient	625	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55∼+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I _E =10μA, I _C =0	6			V
Collector cut-off current	I _{CEX}	V _{CE} =30V, V _{EB(off)} =3V			50	nA
Collector cut-off current	I _{CBO}	V _{CB} = 60V, I _E =0			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			100	nA
	h _{FE(1)}	V _{CE} =1V, I _C =10mA	100		300	
DC current gain	h _{FE(2)}	V _{CE} =1V, I _C =50mA	60			
	h _{FE(3)}	V _{CE} =1V, I _C =100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50mA, I _B =5mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =50mA, I _B =5mA			0.95	٧
Transition frequency	f _T	V _{CE} =20V,I _C =10mA, f=100MHz	300			MHz
Dolov timo	t _d	V_{CC} =3V, $V_{BE(off)}$ =-0.5V I_{C} =10mA,		35	ns	
Delay time		I _{B1} =1mA				
Rise time		V_{CC} =3V, $V_{BE(off)}$ =-0.5V I_{C} =10mA,		35		ns
KISE UIIIE	t _r	I _{B1} =1mA				
Storage time	t _s	$V_{CC}=3V$, $I_{C}=10mA$, $I_{B1}=I_{B2}=1mA$			200	ns
Fall time	t _f	V _{CC} =3V, I _C =10mA, I _{B1} = I _{B2} =1mA			50	ns

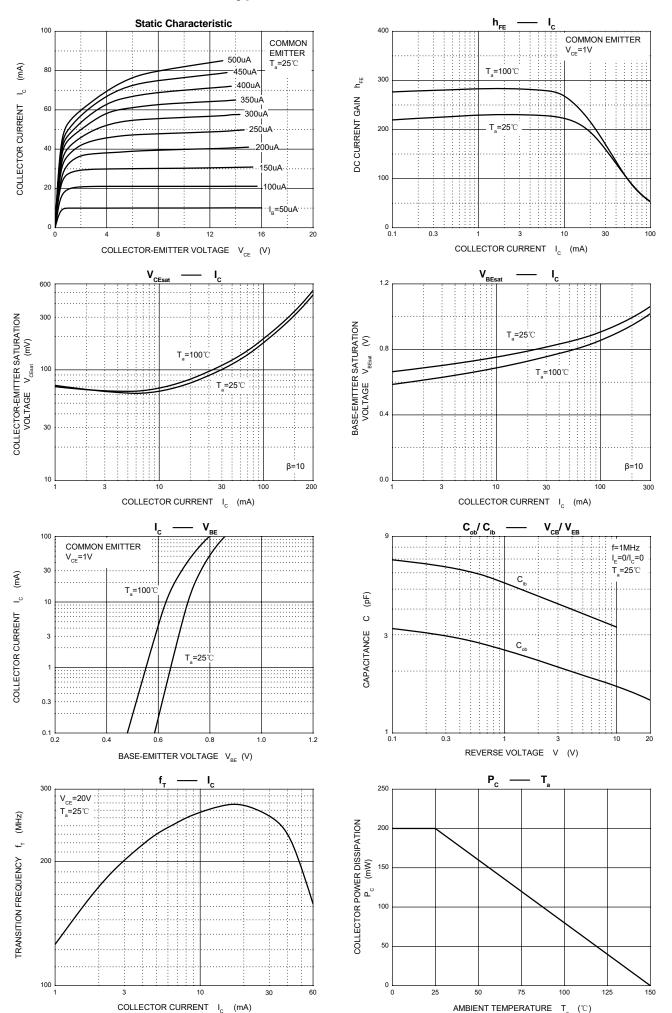
CLASSIFICATION OF h_{FE(1)}

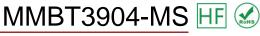
HFE	100-300		
RANK	L	н	
RANGE	100 - 200	200 - 300	

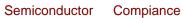
Semiconductor

Compiance

Typical Characteristics

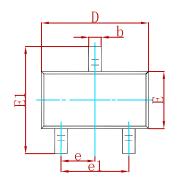


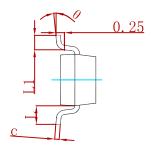


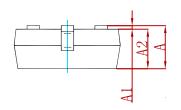




PACKAGE MECHANICAL DATA

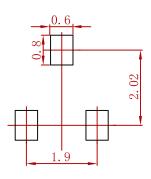






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950) TYP	0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMBT3904-MS	SOT-23	3000



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